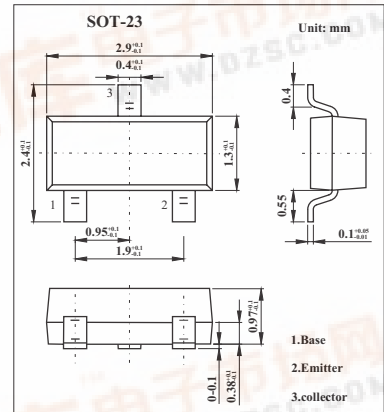


SMD Type Transistors

NPN General Purpose Transistors  
BCX20

■ Features

- General Purpose Transistors.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V <sub>CES</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	25	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	800	A
Collector dissipation	P <sub>C</sub>	310	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Max	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	25		V
Collector-emitter breakdown voltage	BV <sub>CES</sub>	I <sub>C</sub> = 100μA, V <sub>BE</sub> = 0	30		V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CE</sub> = 20V, V <sub>BE</sub> = 0		100	nA
Emitter-base cut-off current	I <sub>EBO</sub>	V <sub>BE</sub> = 5V, I <sub>C</sub> = 0		10	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 100mA	100	600	
		V <sub>CE</sub> = 1V, I <sub>C</sub> = 300mA	70		
		V <sub>CE</sub> = 1V, I <sub>C</sub> = 500mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		0.62	V
Base-emitter saturation voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = 1A, I <sub>B</sub> = 500mA		1.2	V

■ Marking

Marking	U2
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